



ACE1551A

N-Channel Enhancement Mode MOSFET

Description

The ACE1551A is the N-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

Features

- N-Channel
20V/0.95A, $R_{DS(ON)}=380m\Omega @ V_{GS}=4.5V$
20V/0.75A, $R_{DS(ON)}=450m\Omega @ V_{GS}=2.5V$
20V/0.65A, $R_{DS(ON)}=800m\Omega @ V_{GS}=1.8V$
20V/0.65A, $R_{DS(ON)}=1000m\Omega @ V_{GS}=1.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

Applications

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

Absolute Maximum Ratings

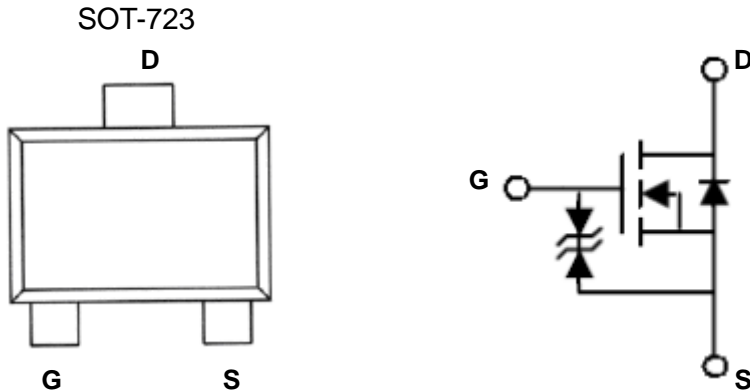
Parameter		Symbol	Max	Unit
Drain-Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V_{GSS}	±12	V
Continuous Drain Current ($T_J=150^{\circ}C$)	$T_A=25^{\circ}C$	I_D	0.65	A
Pulsed Drain Current		I_{DM}	4	A
Continuous Source Current (Diode Conduction)		I_S	0.3	A
Power Dissipation	$T_A=25^{\circ}C$	P_D	0.15	W
Operating Junction Temperature / Storage Temperature Range		T_J/T_{STG}	-55/150	$^{\circ}C$



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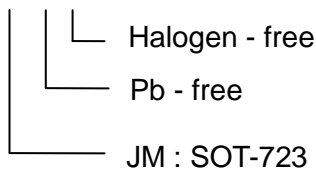
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Packaging Type



Ordering information

ACE1551A XX + H



Electrical Characteristics

$T_A=25^{\circ}\text{C}$, unless otherwise specified.

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\ \mu A$	20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_{DS}=250\ \mu A$	0.35		1.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			30	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
		$V_{DS}=20V, V_{GS}=0V, T_J=55^{\circ}\text{C}$			5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 4.5V, V_{GS} = 5V$	0.7			A
Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=0.95A$		0.26	0.38	Ω
		$V_{GS}=2.5V, I_D=0.75A$		0.32	0.45	
		$V_{GS}=1.8V, I_D=0.65A$		0.42	0.8	
		$V_{GS}=1.5V, I_D=0.65A$		0.5	1.0	
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=0.4A$		1.0		S
Diode Forward Voltage	V_{SD}	$I_{SD}=0.15A, V_{GS}=0V$		0.8	1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=4.5V, I_D=0.6A$		1.2	1.5	nC
Gate-Source Charge	Q_{gs}			0.2		

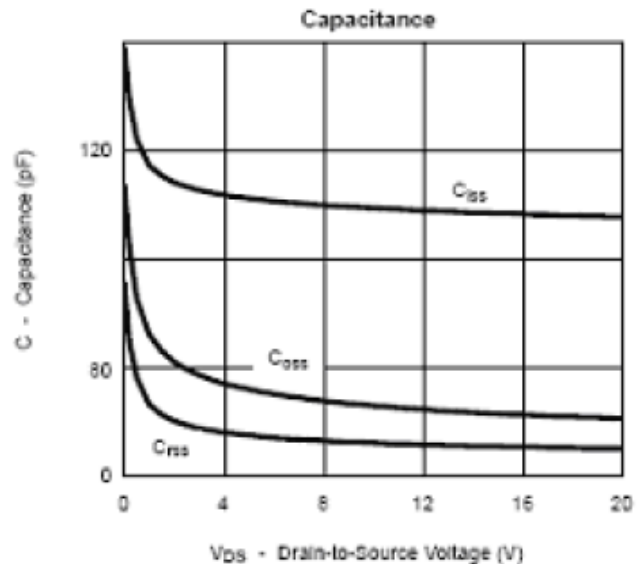
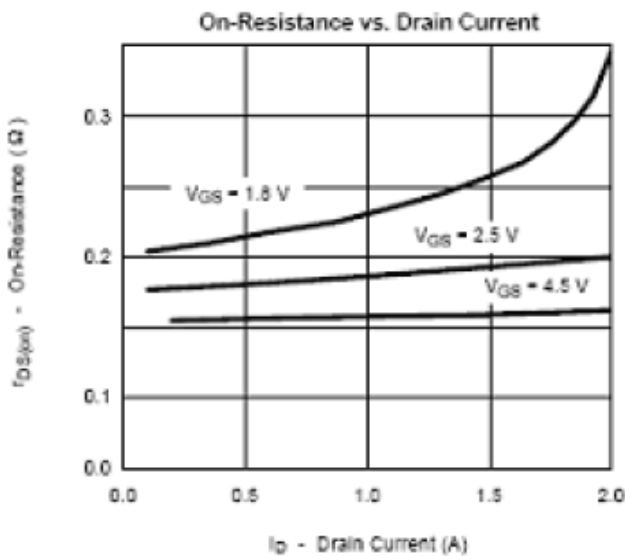
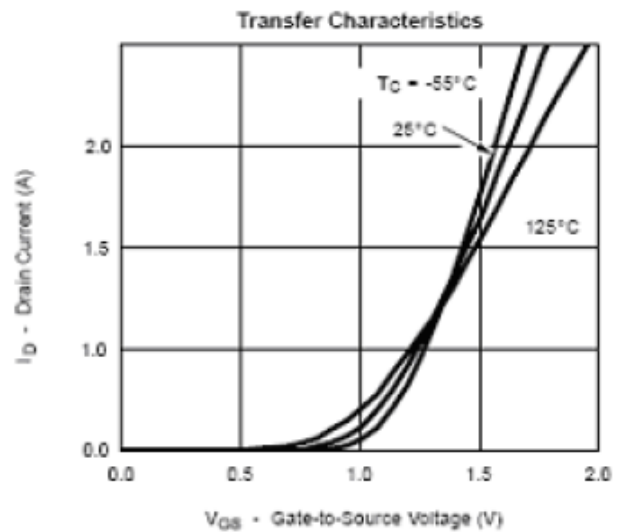
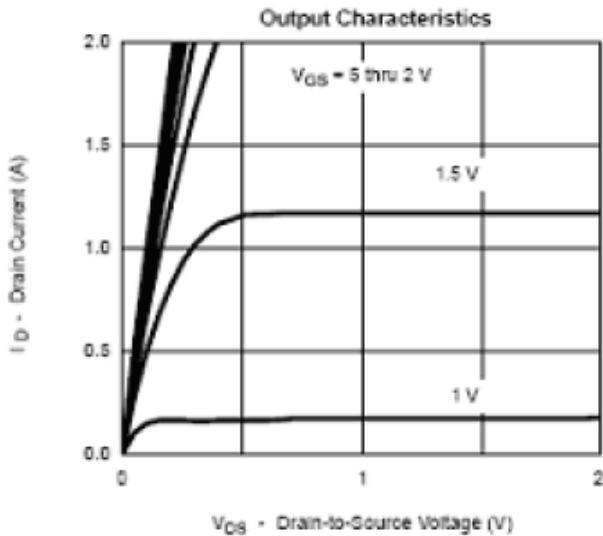


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Gate-Drain Charge	Q_{gd}			0.3		
Turn-On Time	$t_d(on)$	$V_{GEN}=4.5V, I_D=0.5A, V_{DD}=10V,$ $R_G=6\Omega, R_L=10\Omega$		5	10	nS
	t_r			8	15	
Turn-Off Time	$t_d(off)$			10	18	
	t_f			1.2	2.8	

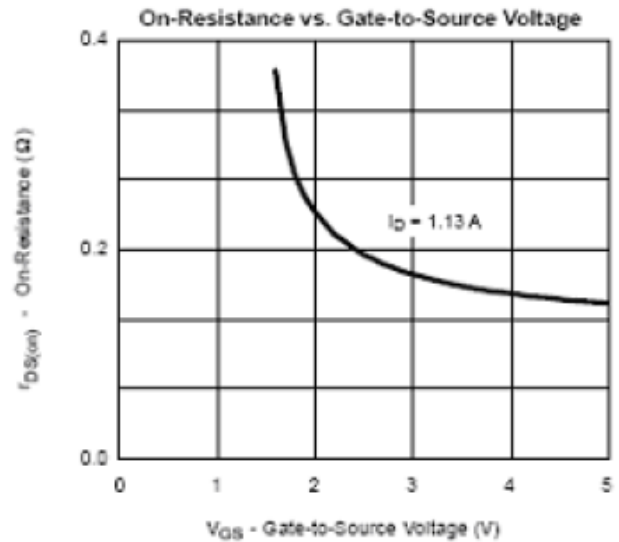
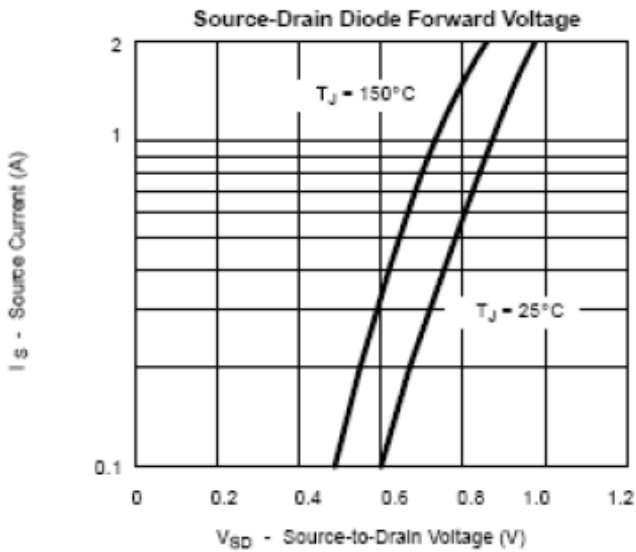
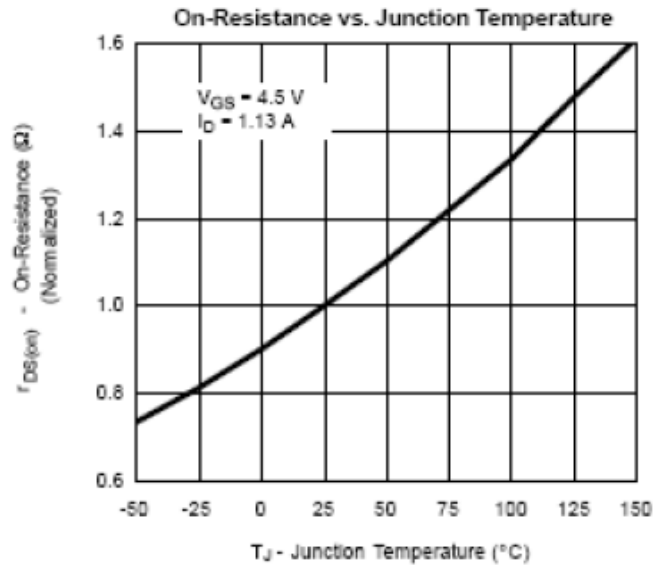
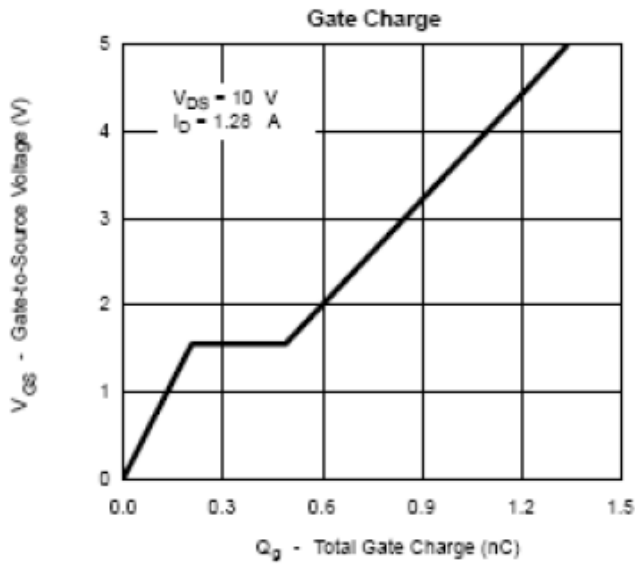
Typical Performance Characteristics





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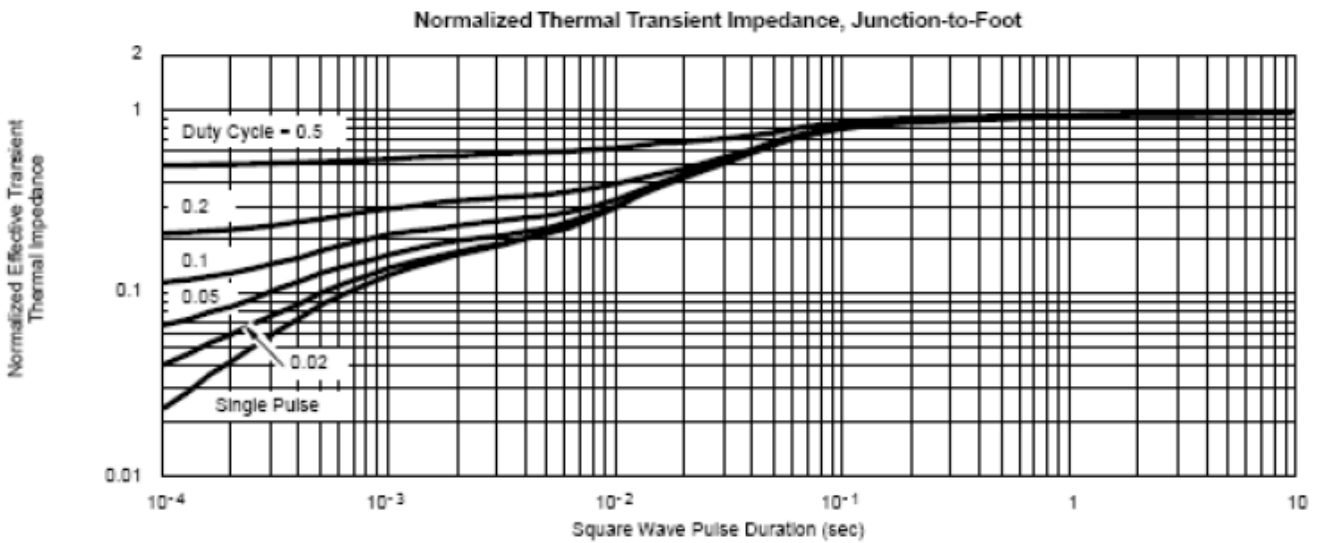
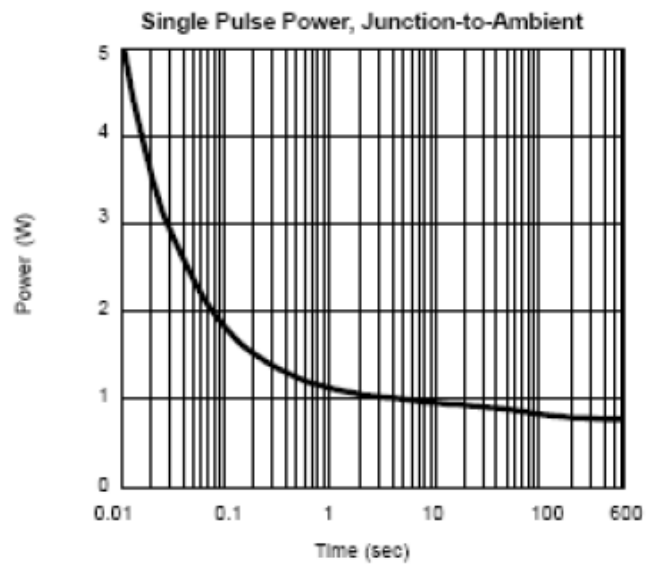
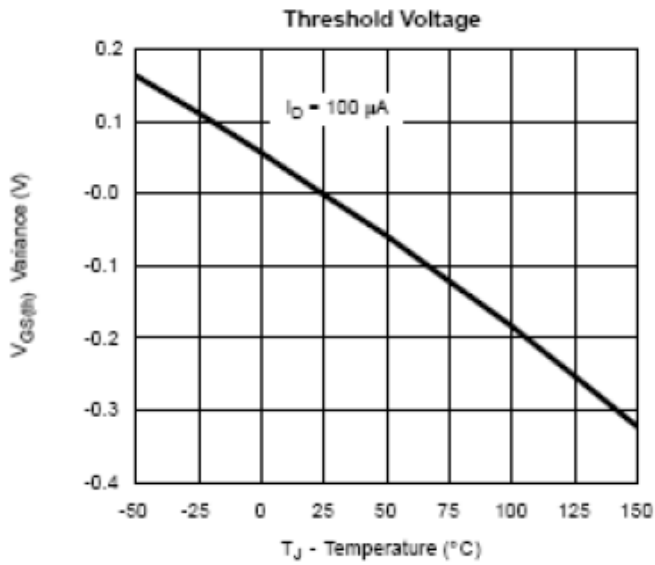
Typical Performance Characteristics





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Typical Performance Characteristics



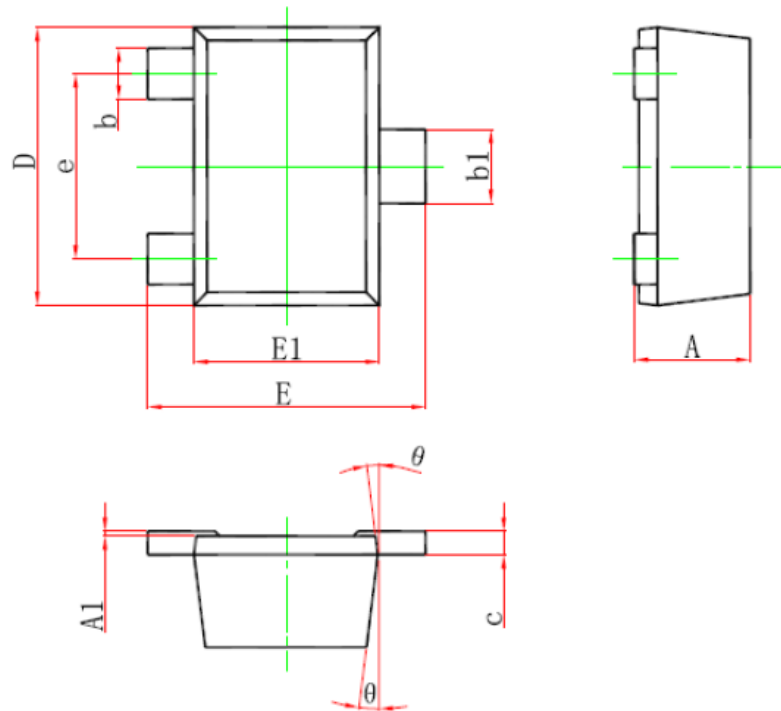


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Packing Information

SOT-723



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A		0.500		0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
c		0.150		0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
e	0.800TYP.		0.031TYP.	
θ	7° REF.		7° REF.	



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Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As sued herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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